DATA SHEET
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Silicon Carbide (SiC) MOSFET – EliteSiC, 20 mohm, 1200 V, M1, TO-247-4L

NTH4L020N120SC1

Features

Typ. $R_{DS(on)}$ = 20 mΩ
Ultra Low Gate Charge ($Q_{G(tot)}$ = 220 nC)
High Speed Switching with Low Capacitance (C_{oss} = 258 pF)
100% Avalanche Tested
T_J = 175°C
This Device is Halide Free and RoHS Compliant with exemption 7a, Pb Free 2LI (on second level interconnection)

Typical Applications

UPS
DC-DC Converter
Boost Inverter

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	1200	V
Gate to Source Voltage	V_{GS}		

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Table 1. THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Max	Unit
Junction to Case Steady State (Note 2)	$R_{\theta JC}$	0.3	°C/W
Junction to Ambient			

Table 2. ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified) (continued)

Parameter	Max	Unit

TO−247−4LD
CASE 340CJ
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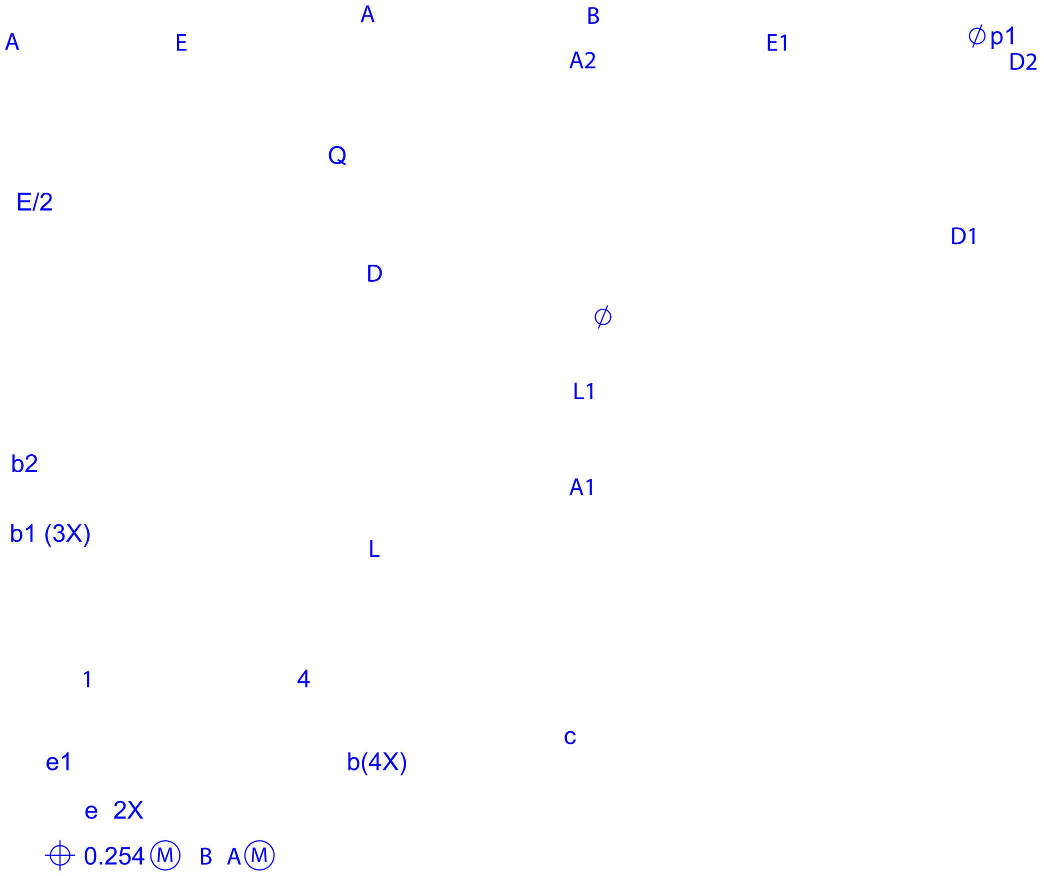

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